these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please cancel claims 17-21 and 76.

Please amend claims 22 and 77-81 as follows:

~~22.~~ (Twice Amended) A method of forming a capacitor, comprising:

forming a capacitor plate, comprising:

providing a first conductive layer in a first environment;

exposing said first conductive layer to a nitrogen free passivation gas; and

depositing a second conductive layer over said first conductive layer, wherein said step of providing a first conductive layer comprises providing a first conductive layer in an oxygen-free environment; and wherein said step of exposing said first conductive layer comprises exposing said first conductive layer to a nitrogen free passivation gas in said oxygen-free environment.

~~77.~~ (Amended) The method of claim ~~78~~ wherein the plasma comprises a selection of N_2/H_2, N_2, and NH_3 plasmas.

~~78.~~ (Amended) A method of forming a capacitor, comprising:

forming a capacitor plate, comprising:

providing a first conductive layer in a first environment;

exposing the first conductive layer to a plasma in a second environment, wherein the first conductive layer is not exposed to oxygen between being

provided in the first environment and being exposed to the plasma in the second environment; and

depositing a second conductive layer over the first conductive layer.

~~79~~ 6. (Amended) A method of forming a capacitor, comprising:

forming a capacitor plate, comprising:

providing a first conductive layer in a first environment;

exposing the first conductive layer to a material selected from the group consisting of B_2H_6, PH_3, and a carbon-silicon compound, in a second environment; and

depositing a second conductive layer over the first conductive layer.

~~80~~ 7. (Amended) The method of claim ~~79~~ 6 wherein exposing the first conductive layer comprises exposing the first conductive layer to a carbon-silicon compound selected from the group consisting of CH_3SiH_3, $(CH_3)_3Si\text{-}Si(CH_3)_3$, and HMDS *in situ*.

~~81~~ 8. (Amended) The method of claim ~~79~~ 6 wherein exposing the first conductive layer comprises exposing the first conductive layer to a carbon-silicon compound selected from the group consisting of CH_3SiH_3, $(CH_3)_3Si\text{-}Si(CH_3)$, and HMDS *ex situ*.